

Title (en)

Method and device for grinding both surfaces of semiconductor wafers

Title (de)

Verfahren und Vorrichtung zum beidseitigen Polieren von Halbleiterscheiben

Title (fr)

Procédé et dispositif de polissage des deux faces de tranches semi-conductrices

Publication

EP 2127810 B1 20110720 (EN)

Application

EP 09161077 A 20090526

Priority

JP 2008139963 A 20080528

Abstract (en)

[origin: EP2127810A1] A method of grinding semiconductor wafers including simultaneously grinding both surfaces of multiple semiconductor wafers being ground by rotating the multiple semiconductor wafers between a pair of upper and lower rotating surface plates in a state where the multiple wafers are held on a carrier so that centers of the multiple wafers are positioned on a circumference of a single circle, wherein a ratio of an area of a circle passing through the centers of the multiple wafers to an area of one of the multiple wafers is greater than or equal to 1.33 but less than 2.0; a rotational speed of the multiple wafers falls within a range of 5 to 80 rpm; and the grinding of the multiple wafers with the rotating surface plates are conducted with fixed abrasive grains in the presence of an alkali solution.

IPC 8 full level

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